

# IRL2203NS-VB Datasheet

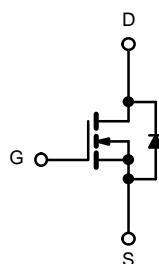
## N-Channel 30-V (D-S) MOSFET

### PRODUCT SUMMARY

V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (Ω)	I <sub>D</sub> (A) <sup>a, e</sup>	Q <sub>g</sub> (Typ)
30	0.0024 at V <sub>GS</sub> = 10 V	98	82 nC
	0.0027 at V <sub>GS</sub> = 4.5 V	98	

### FEATURES

- TrenchFET® Power MOSFET
- 100 % R<sub>g</sub> and UIS Tested
- Compliant to RoHS Directive 2011/65/EU



N-Channel MOSFET

### APPLICATIONS

- OR-ing
- Server
- DC/DC

### ABSOLUTE MAXIMUM RATINGS (T<sub>A</sub> = 25 °C, unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V <sub>DS</sub>	30	V
Gate-Source Voltage	V <sub>GS</sub>	± 20	
Continuous Drain Current (T <sub>J</sub> = 175 °C)	T <sub>C</sub> = 25 °C	98 <sup>a, e</sup>	A
	T <sub>C</sub> = 70 °C	98 <sup>e</sup>	
	T <sub>A</sub> = 25 °C	28.8 <sup>b, c</sup>	
	T <sub>A</sub> = 70 °C	27 <sup>b, c</sup>	
Pulsed Drain Current	I <sub>DM</sub>	300	
Avalanche Current Pulse	I <sub>AS</sub>	36	
Single Pulse Avalanche Energy	E <sub>AS</sub>	64.8	
Continuous Source-Drain Diode Current	T <sub>C</sub> = 25 °C	90 <sup>a, e</sup>	
	T <sub>A</sub> = 25 °C	3.13 <sup>b, c</sup>	
Maximum Power Dissipation	T <sub>C</sub> = 25 °C	250 <sup>a</sup>	W
	T <sub>C</sub> = 70 °C	175	
	T <sub>A</sub> = 25 °C	3.75 <sup>b, c</sup>	
	T <sub>A</sub> = 70 °C	2.63 <sup>b, c</sup>	
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 175	°C

### THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typ.	Max.	Unit
Maximum Junction-to-Ambient <sup>b, d</sup>	R <sub>thJA</sub>	32	40	°C/W
Maximum Junction-to-Case	R <sub>thJC</sub>	0.5	0.6	

Notes:

a. Based on T<sub>C</sub> = 25 °C.

b. Surface mounted on 1" x 1" FR4 board.

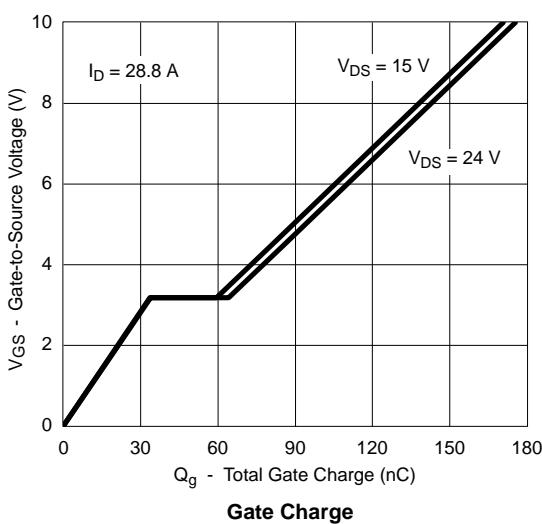
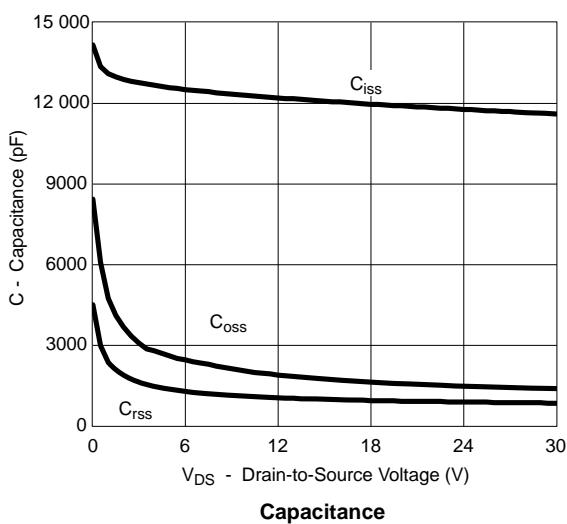
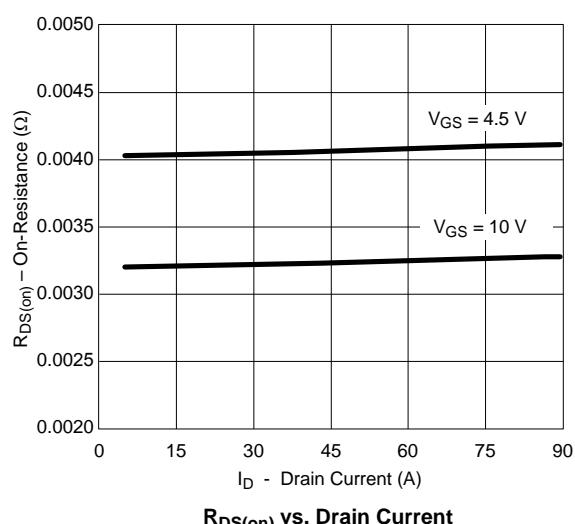
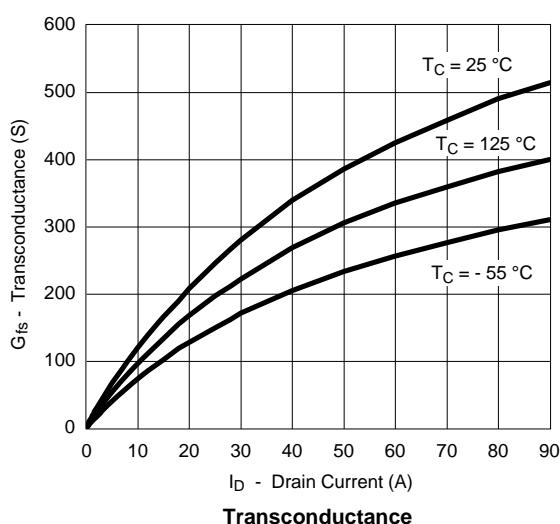
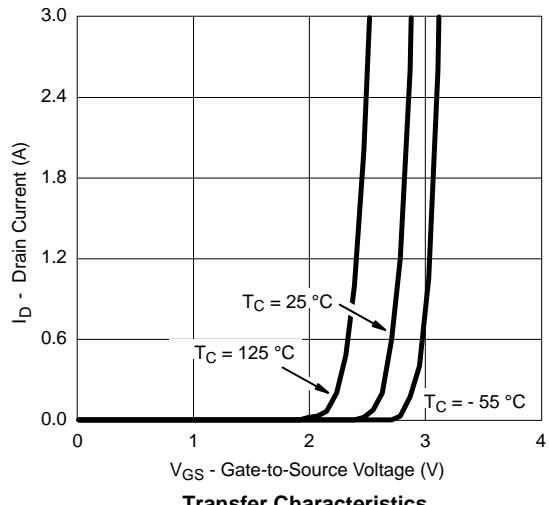
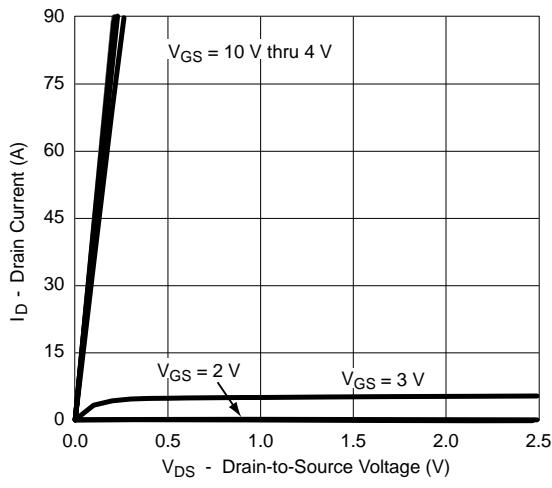
c. t = 10 sec.

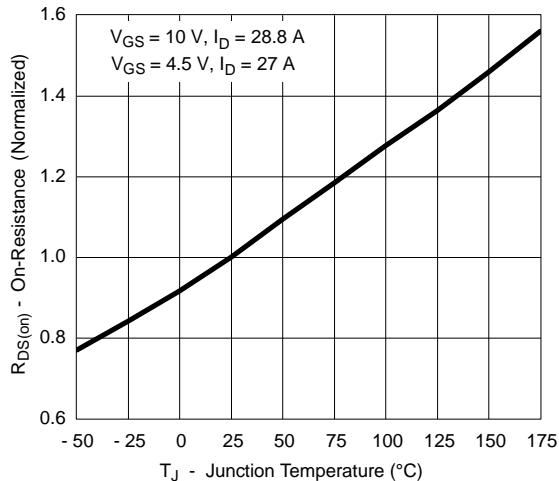
d. Maximum under steady state conditions is 90 °C/W.

e. Calculated based on maximum junction temperature. Package limitation current is 90 A.

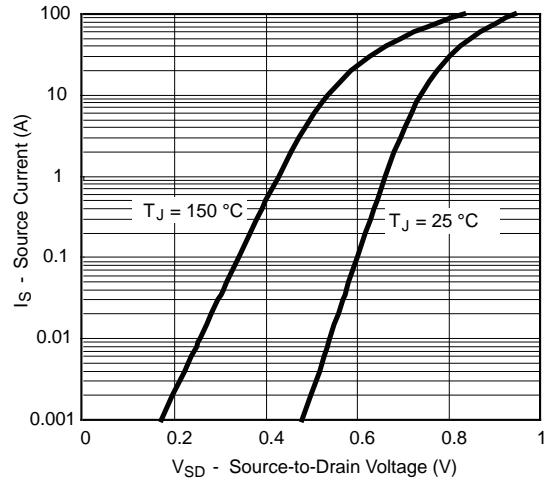
**SPECIFICATIONS** ( $T_J = 25^\circ\text{C}$ , unless otherwise noted)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0 \text{ V}$ , $I_D = 250 \mu\text{A}$	30			V
$V_{DS}$ Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = 250 \mu\text{A}$		35		mV/°C
$V_{GS(\text{th})}$ Temperature Coefficient	$\Delta V_{GS(\text{th})}/T_J$			- 7.5		
Gate-Source Threshold Voltage	$V_{GS(\text{th})}$	$V_{DS} = V_{GS}$ , $I_D = 250 \mu\text{A}$	1.5		2.5	V
Gate-Source Leakage	$I_{GSS}$	$V_{DS} = 0 \text{ V}$ , $V_{GS} = \pm 20 \text{ V}$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 30 \text{ V}$ , $V_{GS} = 0 \text{ V}$		1		$\mu\text{A}$
		$V_{DS} = 30 \text{ V}$ , $V_{GS} = 0 \text{ V}$ , $T_J = 55^\circ\text{C}$			10	
On-State Drain Current <sup>a</sup>	$I_{D(\text{on})}$	$V_{DS} \geq 5 \text{ V}$ , $V_{GS} = 10 \text{ V}$	90			A
Drain-Source On-State Resistance <sup>a</sup>	$R_{DS(\text{on})}$	$V_{GS} = 10 \text{ V}$ , $I_D = 28.8 \text{ A}$		0.0024		$\Omega$
		$V_{GS} = 4.5 \text{ V}$ , $I_D = 27 \text{ A}$		0.0027		
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = 15 \text{ V}$ , $I_D = 28.8 \text{ A}$		160		S
<b>Dynamic<sup>b</sup></b>						
Input Capacitance	$C_{iss}$	$V_{DS} = 15 \text{ V}$ , $V_{GS} = 0 \text{ V}$ , $f = 1 \text{ MHz}$		12065		pF
Output Capacitance	$C_{oss}$			1725		
Reverse Transfer Capacitance	$C_{rss}$			970		
Total Gate Charge	$Q_g$	$V_{DS} = 15 \text{ V}$ , $V_{GS} = 10 \text{ V}$ , $I_D = 28.8 \text{ A}$		171	257	nC
Gate-Source Charge	$Q_{gs}$	$V_{DS} = 15 \text{ V}$ , $V_{GS} = 4.5 \text{ V}$ , $I_D = 28.8 \text{ A}$		81.5	123	
Gate-Drain Charge	$Q_{gd}$			34		
Gate Resistance	$R_g$			29		
Turn-On Delay Time	$t_{d(\text{on})}$	$V_{DD} = 15 \text{ V}$ , $R_L = 0.625 \Omega$ $I_D \approx 24 \text{ A}$ , $V_{GEN} = 10 \text{ V}$ , $R_g = 1 \Omega$		1.4	2.1	$\Omega$
Rise Time	$t_r$			18	27	ns
Turn-Off Delay Time	$t_{d(\text{off})}$			11	17	
Fall Time	$t_f$			70	105	
Turn-On Delay Time	$t_{d(\text{on})}$			10	15	
Rise Time	$t_r$			55	83	
Turn-Off Delay Time	$t_{d(\text{off})}$	$V_{DD} = 15 \text{ V}$ , $R_L = 0.67 \Omega$ $I_D \approx 22.5 \text{ A}$ , $V_{GEN} = 4.5 \text{ V}$ , $R_g = 1 \Omega$		180	270	ns
Fall Time	$t_f$			55	83	
Notes:				12	18	
a. Pulse test; pulse width $\leq 300 \mu\text{s}$ , duty cycle $\leq 2\%$ .						
b. Guaranteed by design, not subject to production testing.						
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.						

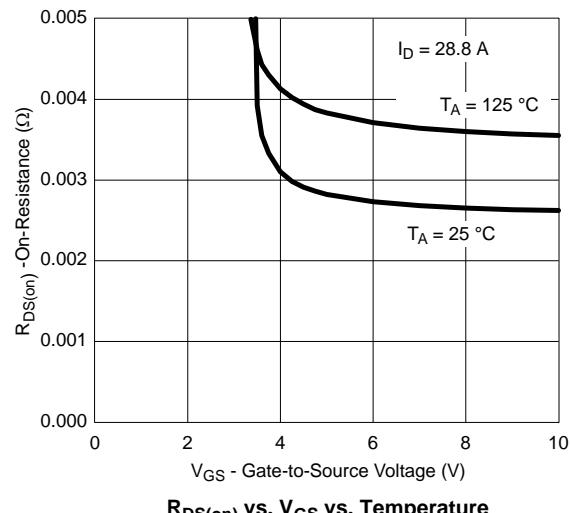
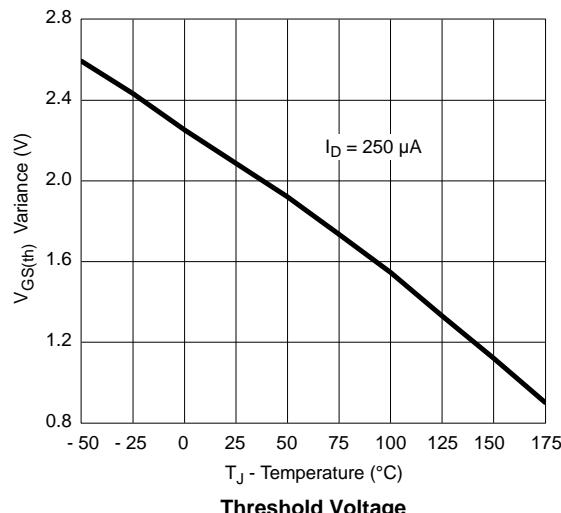
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)


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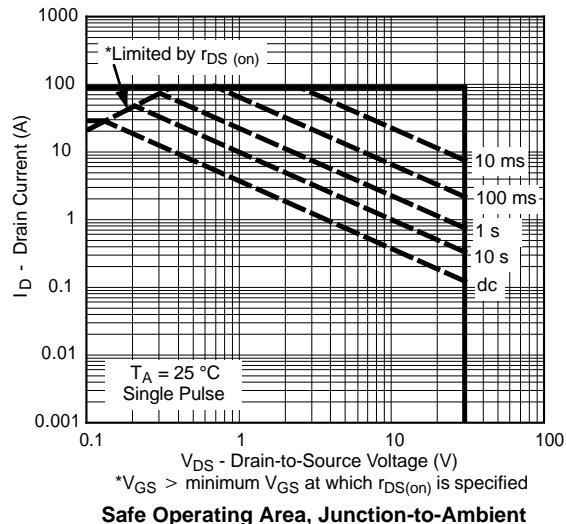
On-Resistance vs. Junction Temperature



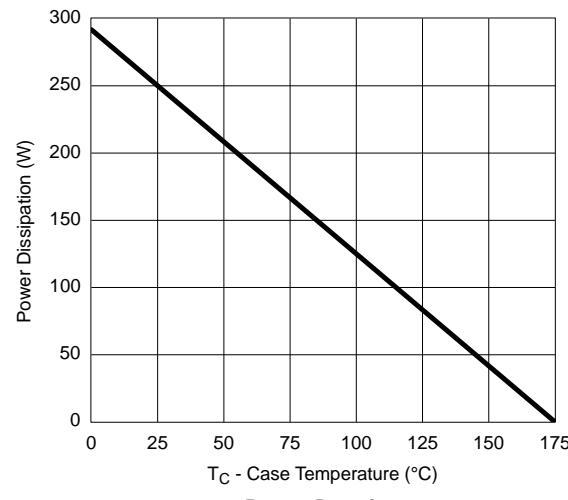
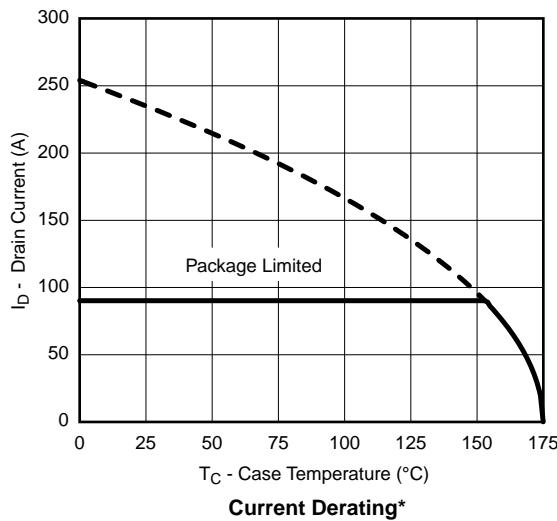
Forward Diode Voltage vs. Temperature

 $R_{DS(on)}$  vs.  $V_{GS}$  vs. Temperature

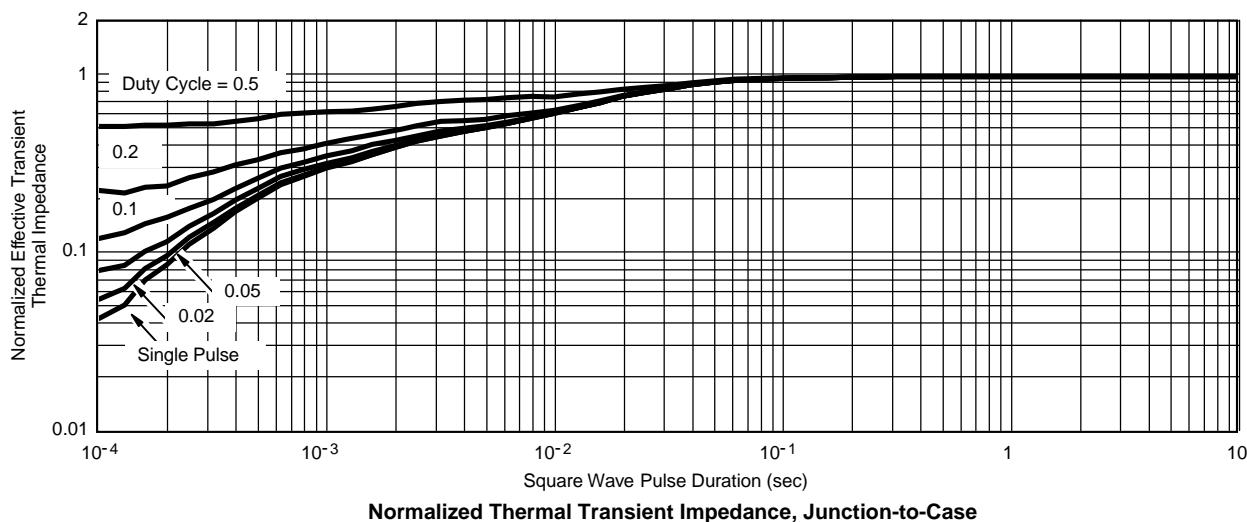
Threshold Voltage

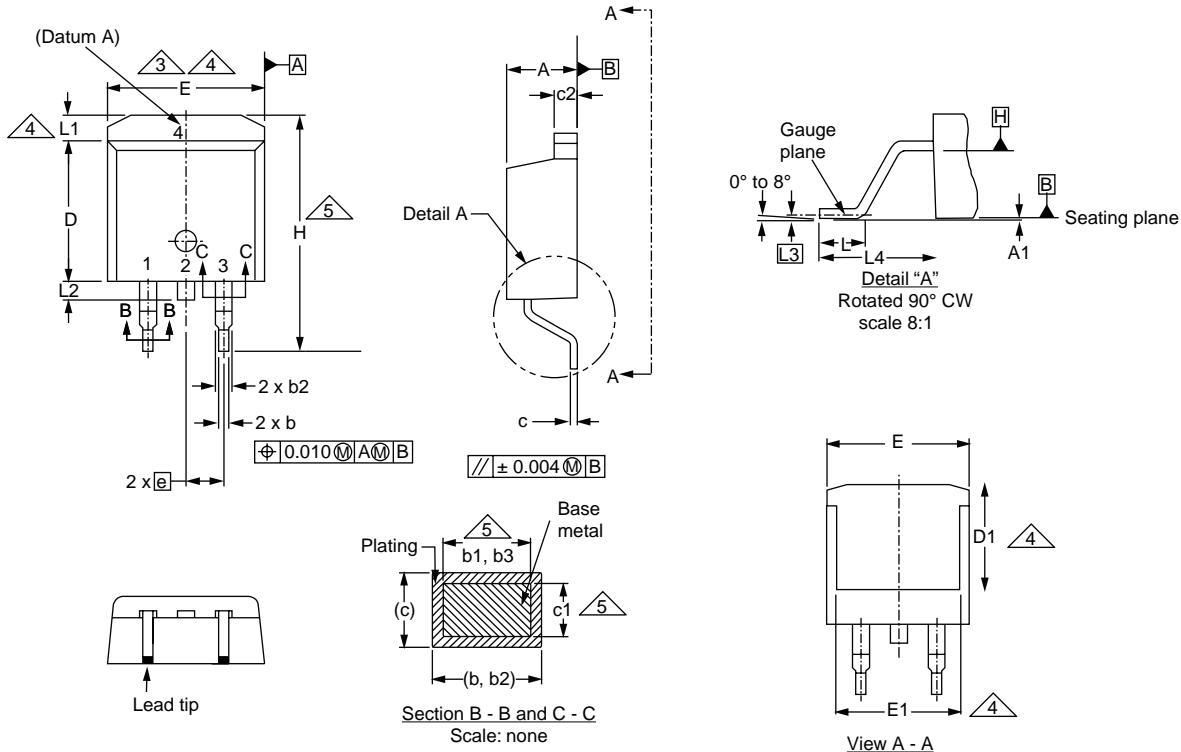


Safe Operating Area, Junction-to-Ambient

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)


\*The power dissipation  $P_D$  is based on  $T_{J(max)} = 175$  °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



**TO-263AB (HIGH VOLTAGE)**

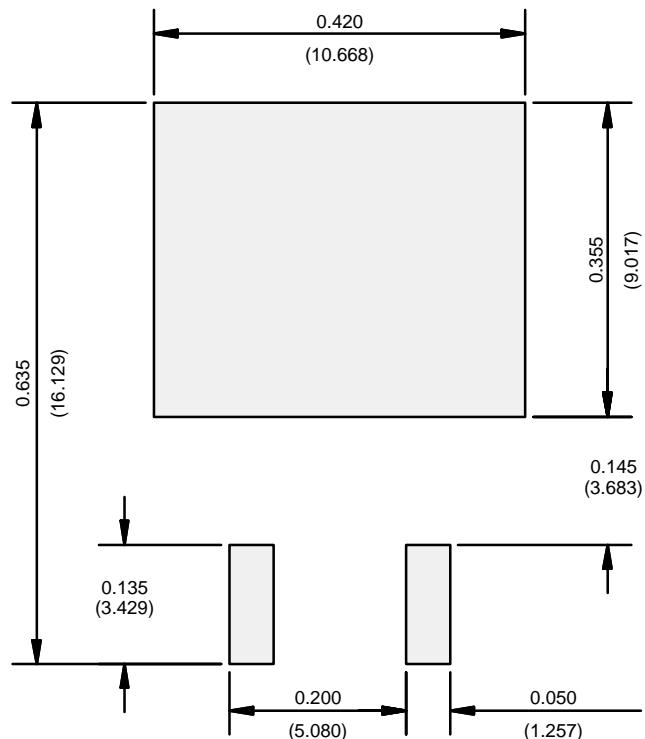
DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.06	4.83	0.160	0.190
A1	0.00	0.25	0.000	0.010
b	0.51	0.99	0.020	0.039
b1	0.51	0.89	0.020	0.035
b2	1.14	1.78	0.045	0.070
b3	1.14	1.73	0.045	0.068
c	0.38	0.74	0.015	0.029
c1	0.38	0.58	0.015	0.023
c2	1.14	1.65	0.045	0.065
D	8.38	9.65	0.330	0.380

ECN: S-82110-Rev. A, 15-Sep-08  
 DWG: 5970

**Notes**

1. Dimensioning and tolerancing per ASME Y14.5M-1994.
2. Dimensions are shown in millimeters (inches).
3. Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body at datum A.
4. Thermal PAD contour optional within dimension E, L1, D1 and E1.
5. Dimension b1 and c1 apply to base metal only.
6. Datum A and B to be determined at datum plane H.
7. Outline conforms to JEDEC outline to TO-263AB.

DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
D1	6.86	-	0.270	-
E	9.65	10.67	0.380	0.420
E1	6.22	-	0.245	-
e	2.54 BSC		0.100 BSC	
H	14.61	15.88	0.575	0.625
L	1.78	2.79	0.070	0.110
L1	-	1.65	-	0.066
L2	-	1.78	-	0.070
L3	0.25 BSC		0.010 BSC	
L4	4.78	5.28	0.188	0.208

**RECOMMENDED MINIMUM PADS FOR D<sup>2</sup>PAK: 3-Lead**

Recommended Minimum Pads  
Dimensions in Inches/(mm)

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